

**Notice of References Cited**

Application/Control No.

10/595,640

Applicant(s)/Patent Under  
Reexamination  
TSUBATA ET AL.

Examiner

EARL N. TAYLOR

Art Unit

2818

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**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-			
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	D	US-			
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	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

**FOREIGN PATENT DOCUMENTS**

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	N	EP 1154036 A1	11-2001	European Patent	ROBERTSON et al.	
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**NON-PATENT DOCUMENTS**

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	V	Ohta et al., Ultrathin fluorinated silicon nitride gate dielectric films formed by remote plasma enhanced chemical vapor deposition employing NH3 and SiF4, Journal of Applied Physics, Vol. 90, No. 4, 2001, pp. 1955-1961
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
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